

**Photovoltaic By-Pass Diode
50 Volts, 1.0 Amps**

PRODUCT PREVIEW

DESCRIPTION

Large area diode chip for medium current photovoltaic by-pass applications, or for higher current hybrid applications. The device is rated for 1A for applications where the device will be exposed to substantial radiation flux (space). For other applications, it may be operated at higher currents. A version with attached leads is available.

IMPORTANT: For the most current data, consult MICROSEMI's website: <http://www.microsemi.com>

KEY FEATURES

- Oxide passivated structure for very low leakage currents
- Epitaxial structure minimizes forward voltage drop
- Triangular shape to fit in corner near flat of photovoltaic cell
- Forward voltage decreases with radiation exposure
- Targeted for terrestrial applications with silicon photovoltaic cells
- Thin construction for fit with photovoltaic cells

APPLICATIONS/BENEFITS

- Increases efficiency of photovoltaic arrays
- Protects photovoltaic cells from reverse voltage

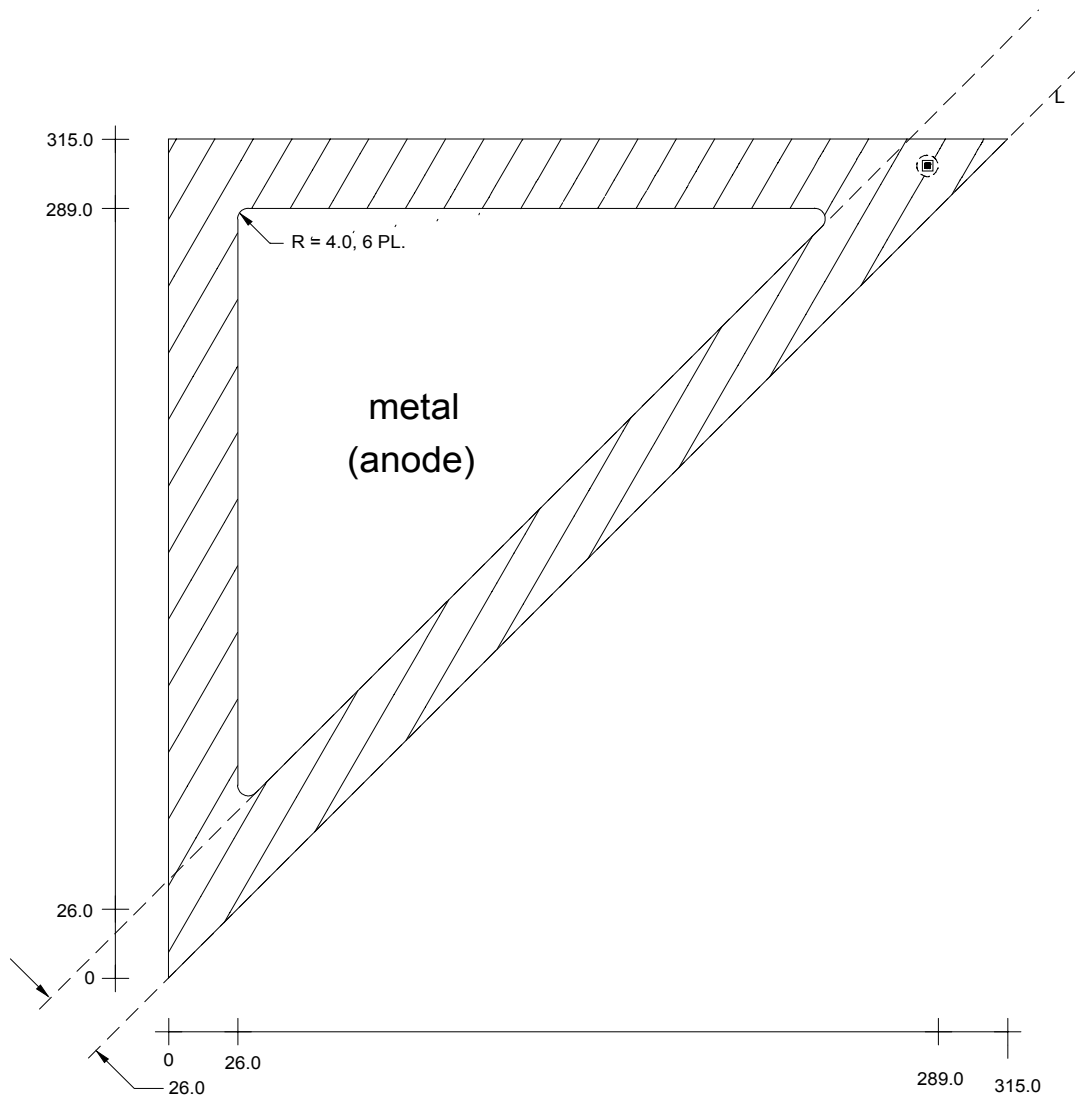
MAXIMUM RATINGS @ 25°C (UNLESS OTHERWISE SPECIFIED)

Description	Symbol	Max.	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	50	Volts
Working Peak Reverse Voltage	V_{RWM}	50	Volts
DC Blocking Voltage	V_R	50	Volts
Average Rectified Forward Current, $T_c \leq 135^\circ\text{C}$	$I_{F(ave)}$	1.0	Amps
Junction Temperature Range	T_j	-65 to +150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-65 to +200	$^\circ\text{C}$

ELECTRICAL PARAMETERS

Description	Symbol	Conditions	Min	Typ.	Max	Unit
Reverse (Leakage) Current (in dark)	IR_{25}	$VR = 4 \text{ Vdc}, Ta = 25^\circ\text{C}$		10		nA
	IR_{25}	$VR = 50 \text{ Vdc}, Ta = 25^\circ\text{C}$		20	200	nA
Forward Voltage pulse test, $pw = 300 \mu\text{s}$	$VF1$	$IF = 400 \text{ mA}, Ta = 25^\circ\text{C}$		750	775	mV
	$VF2$	$IF = 1.0 \text{ A}, Ta = 25^\circ\text{C}$		770	800	mV
Junction Capacitance	$Cj1$	$VR = 4 \text{ Vdc}$		1050	1300	pF
Breakdown Voltage	BVR	$IR = 200 \mu\text{A}, Ta = 25^\circ\text{C}$	50	90		V

Mechanical Outline



MXP1144

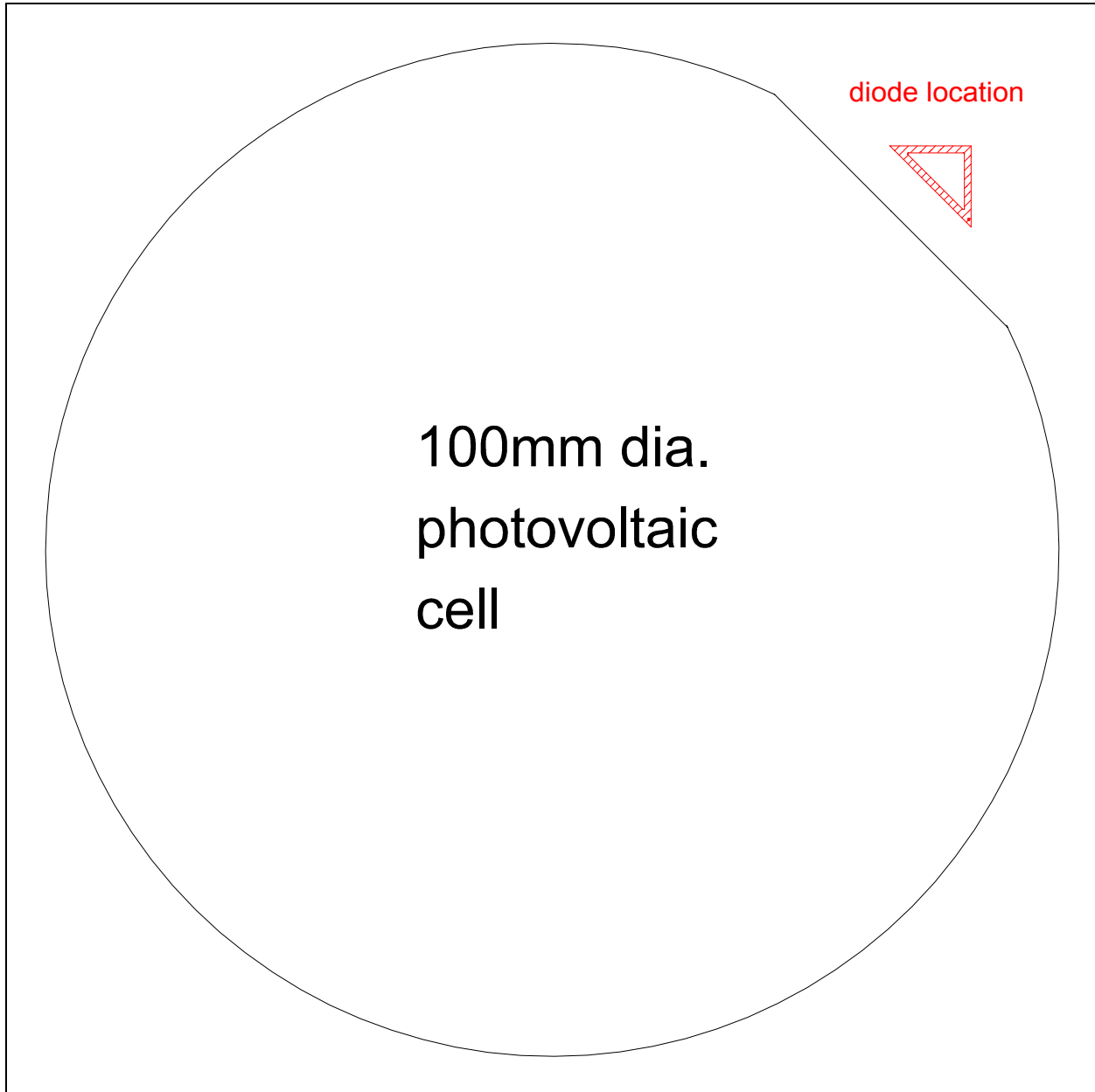
all dimensions in mils

Standard die thickness is 5.0 +/- 0.5 mils

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Typical location with 100mm diameter photovoltaic cell





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NOTES

www.Microsemi.com

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